

LETTERS

Amorphous Si/SiO₂ distributed Bragg reflectors with transfer printed single-crystalline Si nanomembranes

Minkyu Cho, Jung-Hun Seo, Deyin Zhao, Jaeseong Lee, Kanglin Xiong, Xin Yin, Yonghao Liu, Shih-Chia Liu, Munho Kim, Tong J. Kim, Xudong Wang, Weidong Zhou and Zhenqiang Ma
J. Vac. Sci. Technol. B **34**, 040601 (2016);
<http://dx.doi.org/10.1116/1.4945998>

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V-band monolithic microwave integrated circuit with continuous wave output power of >23.5 dBm using conventional AlGaN/GaN-on-Si structure

Dong-Hwan Kim, Su-Keun Eom, Myoung-Jin Kang, Jun-Seok Jeong, Kwang-Seok Seo and Ho-Young Cha
J. Vac. Sci. Technol. B **34**, 040602 (2016);
<http://dx.doi.org/10.1116/1.4947005>

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Study of copper diffusion in RF magnetron sputtered boron carbon nitride thin films

Adithya Prakash and Kalpathy B. Sundaram
J. Vac. Sci. Technol. B **34**, 040603 (2016);
<http://dx.doi.org/10.1116/1.4948399>

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Resonant cavity germanium photodetector via stacked single-crystalline nanomembranes

Minkyu Cho, Jung-Hun Seo, Munho Kim, Jaeseong Lee, Dong Liu, Weidong Zhou, Zongfu Yu and Zhenqiang Ma
J. Vac. Sci. Technol. B **34**, 040604 (2016);
<http://dx.doi.org/10.1116/1.4948531>

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Toward synthesis of oxide films on graphene with sputtering based processes

Patrik Ahlberg, Tomas Nyberg, Shi-Li Zhang, Zhi-Bin Zhang and Ulf Jansson
J. Vac. Sci. Technol. B **34**, 040605 (2016);
<http://dx.doi.org/10.1116/1.4949565>

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High-temperature Ta diffusion in the grain boundary of thin Cu films

Shabnam Mardani, Hans Norström, Ulf Smith and Shi-Li Zhang
J. Vac. Sci. Technol. B **34**, 040606 (2016);
<http://dx.doi.org/10.1116/1.4950744>

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Magnesium-gold binary alloy for organic light-emitting diodes with high corrosion resistance

Hiroya Arai, Hajime Nakanotani, Kei Morimoto and Chihaya Adachi
J. Vac. Sci. Technol. B **34**, 040607 (2016);
<http://dx.doi.org/10.1116/1.4952408>

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Tilted ion implantation as a cost-efficient sublithographic patterning technique

Sang Wan Kim, Peng Zheng, Kimihiko Kato, Leonard Rubin and Tsu-Jae King Liu
J. Vac. Sci. Technol. B **34**, 040608 (2016);
<http://dx.doi.org/10.1116/1.4953085>

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Compact mirror-tunable laser interference system for wafer-scale patterning of grating structures with flexible periodicity

Yung-Jr Hung, Ping-Chien Chang, Yu-Nung Lin and Jia-Jin Lin
J. Vac. Sci. Technol. B **34**, 040609 (2016);
<http://dx.doi.org/10.1116/1.4955172>

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ELECTRONIC & OPTOELECTRONIC MATERIALS, DEVICES & PROCESSING

Nondestructive cleaning of the LaAlO₃/SrTiO₃ surface with ultraviolet light and ozone

Eric Andersson, Pier Paolo Aurino, Dag Winkler and Alexei Kalabukhov
J. Vac. Sci. Technol. B **34**, 041201 (2016);
<http://dx.doi.org/10.1116/1.4944660>

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Investigation of the interface between LPCVD-SiN_x gate dielectric and III-nitride for AlGaN/GaN MIS-HEMTs

Zhaoyang Liu, Sen Huang, Qilong Bao, Xinhua Wang, Ke Wei, Haojie Jiang, Hushan Cui, Junfeng Li, Chao Zhao, Xinyu Liu, Jinhan Zhang, Qi Zhou, Wanjun Chen, Bo Zhang and Lifang Jia
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<http://dx.doi.org/10.1116/1.4944662>

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Initiation strategies for simultaneous control of antiphase domains and stacking faults in GaAs solar cells on Ge

Joseph Faucher, Taizo Masuda and Minjoo Larry Lee
J. Vac. Sci. Technol. B **34**, 041203 (2016);
<http://dx.doi.org/10.1116/1.4945659>

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Temperature dependence of the dielectric function and interband transitions of pseudomorphic GeSn alloys

Vijay Richard D'Costa, Daniel Schmidt, Wei Wang and Yee-Chia Yeo

J. Vac. Sci. Technol. B **34**, 041204 (2016);

<http://dx.doi.org/10.1116/1.4946759>

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Effect of porosity and pore size on dielectric constant of organosilicate based low-k films: An analytical approach

Alexander P. Palov, Ekaterina N. Voronina, Tatyana V. Rakhimova, Dmitri V.

Lopaev, Sergey M. Zyryanov, Yuri A. Mankelevich, Mikhail B. Krishtab and Mikhail R. Baklanov

J. Vac. Sci. Technol. B **34**, 041205 (2016);

<http://dx.doi.org/10.1116/1.4946838>

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***In situ* monitoring of hydrogen desorption from silicon nanoparticles dispersed in a nonthermal plasma**

Thomas Lopez and Lorenzo Mangolini

J. Vac. Sci. Technol. B **34**, 041206 (2016);

<http://dx.doi.org/10.1116/1.4946839>

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Elevated temperature performance of Si-implanted solar-blind β -Ga₂O₃ photodetectors

Shihyun Ahn, Fan Ren, Sooyeoun Oh, Younghun Jung, Jihyun Kim, Michael A.

Mastro, Jennifer K. Hite, Charles R. Eddy Jr. and S. J. Pearton

J. Vac. Sci. Technol. B **34**, 041207 (2016);

<http://dx.doi.org/10.1116/1.4948361>

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Direct observation of x-ray radiation-induced damage to SiO₂/Si interface using multiwavelength room temperature photoluminescence

Jae Hyun Kim, Je Young Park, Chang Hwan Lee, Yeo Jin Yoon, Jin San

Yoo, Toshikazu Ishigaki, Kitaek Kang and Woo Sik Yoo

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<http://dx.doi.org/10.1116/1.4949518>

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X-ray diffraction analysis for step and linearly graded In_xGa_{1-x}As/GaAs (001) heterostructures using various hkl reflections

Fahad A. Althowibi, Paul B. Rago and John E. Ayers

J. Vac. Sci. Technol. B **34**, 041209 (2016);

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Temperature-dependent electrical instability of p-type SnO thin-film transistors

Jeong-Hwan Lee, Yong-Jin Choi, Chan-Yong Jeong, Chang-Woo Lee and Hyuck-In Kwon

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<http://dx.doi.org/10.1116/1.4949558>

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Comparative study of the differential resistance of GaAs- and GaN-based laser diodes

Xiang Li, Zongshun Liu, Degang Zhao, Desheng Jiang, Ping Chen, Jianjun

Zhu, Jing Yang, Lingcong Le, Wei Liu, Xiaoguang He, Xiaojing Li, Feng

Liang, Liqun Zhang, Jianping Liu, Hui Yang, Yuan Tao Zhang and Guotong Du

J. Vac. Sci. Technol. B **34**, 041211 (2016);

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